Vertex Detector Issues for the LCD

Jim Brau University of Oregon

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Physics of Linear Collider demands the <u>best possible</u> vertex detector performance

> physics signals will be rich in sec. vertices event rates will be limited

CCDs offer the most attractive avenue for achieving this performance (but rad-hardness must improve)

A decade of experience with CCDs in the linear collider environment of SLD has proven their exceptional performance

Active Pixels are being studied in Europe

Larger material thickness (hybrids) Monolithic APDs also being developed (http://hep.ph.liv.ac.uk/~green/lcfi/lcfihome.html)

Outline of Today's Presentation

\Rightarrow Typical and Important Physics Processes

• Higgs, W pairs,

\Rightarrow Detector Design

- Inner radius, magnetic field, #layers, etc.
- Cost exercise

\Rightarrow Radiation environment

- Expected backgrounds
- Radiation damage studies
 - neutron induced damage

\Rightarrow Simulation Study Plans

- optimized detector design
- physics demands

The Vertex Detector will impact most of the physics topics of the LC. For example:

Higgs branching ratios critical test of SM (or measurement of tan β) Higgs self-couplings (Zhh)

SUSY Higgs A $\rightarrow \tau \tau$

Supersymmetry

staus (flavor-dependence of SUSY breaking)

Top

mass, width, etc. Yukawa couplings

W pairs

W's with flavor tagging W/Z discrimination through flavor tagging, or improved mass resolution

Z′

tau polarization

Z Pole

Rb, Ab, B pairs, τ pairs,



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Figure 5: Determination of Higgs boson branching ratios in a variety of decay modes, from [66] The error bars show the expected experimental errors for 500 fb⁻¹ at 350 GeV. The bands show the theoretical errors in the Standard Model predictions.

Battaglia

MSSM h^0 Branching Ratios vs $tg\beta$: Maximal Mixing

Chris Potter

August 11, 2000



Studies now underway (that I am aware of):

Higgs branching ratios - SM, SUSY, vertex optimization Iwasaki, Potter, Sinev

Top quark reconstruction (vertexing/calorimetry issues) Iwasaki

Charm tagging to enhance Strong Symmetry Breaking Sensitivity - aggressive scenarios Walkowiak, Schumm

Radiation backgrounds and masks Maruyama, Markiewicz, et al.

Installation of ZVTOP into LCD software - ROOT - Abe, Iwasaki, Neal - JAS - Walkowiak, Schumm

These studies are needed to justify our choice of vertex detector parameters.

Others?



Chris Potter

August 28, 2000



Critical Issues in Optimizing Flavor Tag:

\Rightarrow track resolution

* determined by technology: CCDs offer very best resolution (but, how good can it be, AND what do we need?)

\Rightarrow outer radius of vertex detector

* constrained by outer detector & budget compact, conventional, ??

 \Rightarrow inner radius

- * limited by LC parameters and detector B field
 ⇒ beam backgrounds
 - \Rightarrow B-field needed to constrain the backgrounds

\Rightarrow radiation immunity

- * design shielding to protect CCDs
- * improve CCD radiation tolerance

Vertex Detector Design

for the future Linear Collider

• Maximum Precision ($< 4 \mu m$)

• Minimal Layer Thickness $(1.2\% X_0 \rightarrow 0.4\% X_0 \rightarrow 0.12\% X_0 \rightarrow 0.06\% X_0)$ SLD-VXD2 SLD-VXD3 Linear Collider stretched

• Minimal Layer 1 Radius $(28 \rightarrow 12 \text{ mm} \rightarrow 5 \text{mm})$ SLD-VXD3 LC Schumm challenge

• Polar Angle Coverage $(\cos \theta \sim 0.9)$

- Standalone Track Finding (perfect linking)
- Layer 1 Readout Between Bunch Trains (4.6 msec)
- Deadtimeless Readout (high trigger rate)

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Cost Estimate Exercise (April/May, 2000)

The VXD3 cost, including contingency, was 1997 k\$ (FY95)

5 barrel LCD detector was estimated to be 3973 k\$ (FY00), without contingency (40%).

Engineering manpower	900k\$
Electronics	500k\$
Mechanics	573k\$
CCD Detectors	2000k\$

Note: this cost estimate does not include beam-pipe, installation, or contingency, which were included in VXD3. For the LCD, they are costed elsewhere.

Radiation Hardness Tests of CCDs

Nick Sinev

(http://blueox.uoregon.edu/~jimbrau/talks/IEEE-99/ieee99.pdf)

Background estimates have varied from 10⁷ n/cm²/year to 10¹¹ n/cm²/year - 2.3 x 10⁹ n/cm²/year (Maruyama-Berkeley2000)

Expected tolerance for CCDs in the range of 10⁹ (C. Damerell)

We need to develop procedures and designs to <u>increase tolerance</u>

More radiation damage studies are called for improve understanding of issues and sensitivity improve radiation hardness flushing techniques supplementary channels bunch compression & clock signal optimization SLD experience during VXD3 commissioning,

an undamped beam was run through the detector, causing radiation damage in the innermost barrel. The damage was observed because we were operating the detector at an elevated temperature (≈220 K).

Reducing the temperature to 190 K ameliorated the damage



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Theory of Radiation Damage

The most important radiation damage in CCDs caused by heavy particles is <u>displacement</u> in the bulk silicon.

1 MeV neutrons can transfer up to 130 keV to PKA. Only 15 eV is needed to displace an atom from the lattice.



Example of simulated tracks of knock-out silicon atoms from a primary knock-out energy of 40 keV. (V.A.J.Van Lint, NIM A253, 453 (1987).)

Vacancy (V) and interstitial silicon (I) pairs are created as a result of atom displacement. More than 90% of such pairs recombine immediately. Those which are not recombined diffuse until they form complexes of two or more vacancies (V2 or V3) or vacancyimpurity (VP, V2O and so on). Such complexes are usually not mobile. Some of them are able to bind electrons, and the bound energy for some of these is about 0.35 - 0.5 eV below the conduction band. These may act as electron traps when empty. If the bound energy is close to the conduction band, (shallow traps) the lifetime of the bound state is so short, that the trapped <u>electron will be released quickly</u> and re-join the charge packet before the packet passes through the trap region. In this case no charge transfer inefficiency will be introduced by the defect.

However, for the <u>deeper levels (close to 0.5 eV</u> below the conduction band) the lifetime of the bound state, which is:

$$\boldsymbol{t} = \frac{e^{(E_c - E_{tr})/kT}}{\boldsymbol{s}_n \boldsymbol{c}_n \boldsymbol{n}_n N_c}$$

is <u>larger than the inter-pixel transfer time</u>, so trapped electrons are removed from the charge packet and released after the packet passes through the trap region. This leads to charge transfer inefficiency. Such inefficiency may be<u>cured</u>, however, <u>by cooling</u> the CCD to a low enough temperature, that the lifetime of the bound electrons in the trap becomes very long, so that the <u>filled traps</u> remain occupied when the next charge packet passes. Filled trap can't capture more electrons, so this trap will not lead to charge transfer inefficiency.



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History of Exposures
(spare SLD VXD3 CCD)(@SLAC
$$\sim 2 \times 10^9 \text{ n/cm}^2$$

Pu(Be)
 $< E_n > \approx 4 \text{ MeV}$ room temperature
Pu(Be)
 $< E_n > \approx 4 \text{ MeV}$ (@SLACAnnealing study100° C for 35 days(@Reactor (I) $\sim 2 \times 10^9 \text{ n/cm}^2$
reactor* neutrons
 $< E_n > \approx 1 \text{ MeV}$ ($\sim 1 \times 10^9 \text{ n/cm}^2$ lower energy)(@Reactor (II) $\sim 1.2 \times 10^9 \text{ n/cm}^2$
reactor* neutrons
 $< E_n > \approx 1 \text{ MeV}$ ($\sim 1 \times 10^9 \text{ n/cm}^2$ lower energy)(@Reactor (II) $\sim 1.2 \times 10^9 \text{ n/cm}^2$
reactor* neutrons
 $< (\sim 190 \text{ K})$
 $< E_n > \approx 1 \text{ MeV}$ ($\sim 1 \times 10^9 \text{ n/cm}^2$ lower energy)Total exposure $\sim 5.2 \times 10^9 \text{ n/cm}^2$
mix of source and reactor
* UC Davis (G. Grim et al)



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Defect Results from Exposures			
	<u># defect (> 6 e⁻)</u> 800,000 pixels	<u># defect (>20e⁻)</u> 800,000 pixels	
Prior to exposure	125	24	
Following 2 × 10 ⁹ n/cm ² (source)	916	160	
Additional $2 \times 10^9 \text{n/cm}^2$ (reactor)	5476	442	
Additional $1.2 \times 10^9 \text{n/cm}^2$ (reactor)	7036	298*	
* this drop in defect count is not understood, but may be related to thermal cycling.			





Issues needing further and refined study:

Dependence of physics performance on vertex detector parameters

Parameters:

Inner radius Outer radius Number of barrels Angular coverage Hit Resolution (pixel size) Background pile-up (layer dependent; related to B)

Study impact of each of these on physics perform.

Performance measures:

Impact parameter resolutions Tagging efficiencies and purities b quarks charm taus Specific channels studies eg. Higgs -> c c-bar

We still need to incorporate vertex recon. (ZVTOP3)into LCD simulation. (we should have this soon)

Radiation backgrounds and design advances to enhance radiation tolerance.

Conclusions Vertex Detection with CCDs at the Linear Collider is quite mature (thanks to SLD), but the unique physics opportunities at the next Linear Collider require further advances. rad-hardening of CCDs, faster CCDs..... Radiation hardness studies of CCDs have started and show promise to provide techniques to deal with the more hostile environment of the higher energy Linear Collider. flushing techniques, etc. \rightarrow but more work is needed Several simulation physics performance studies are underway, and we should these soon to clarify/justify the requirements for the vertex detector.